

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-60V	155mΩ @ V _{GS} = -10V	-2.4A
	240mΩ @ V _{GS} = -4.5V	-1.9A

Features and Benefits

- Rated to +175°C—Ideal for High Ambient Temperature Environments
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

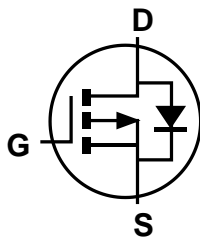
- Battery Charging
- Power Management Functions
- DC-DC Converters
- Load Switch

Mechanical Data

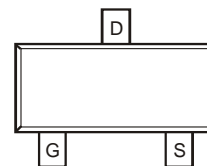
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



Top View



Internal Schematic



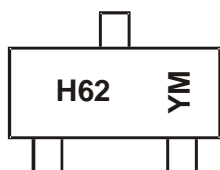
Top View

Ordering Information (Note 5)

Part Number	Case	Packaging
DMPH6250SQ-7	SOT23	3000/Tape & Reel
DMPH6250SQ-13	SOT23	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to <https://www.diodes.com/quality/>.
 5. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



H62 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: F = 2018)
 M = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024				
Code	E	F	G	H	I	J	K	L				
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = -10V	I _D	Steady State T _A = +25°C	-2.4
		T _A = +100°C	-1.5
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I _{DM}	-13	A
Maximum Continuous Body Diode Forward Current (Note 7)	I _S	-1.6	A
Pulsed Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)	I _{SM}	-13	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	0.92	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	R _{θJA}	165	°C/W
Power Dissipation (Note 7)	P _D	1.62	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 7)	R _{θJA}	93.1	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1.0	µA	V _{DS} = -60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	-1.9	-3.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	112	155	mΩ	V _{GS} = -10V, I _D = -2A
		—	149	240		V _{GS} = -4.5V, I _D = -2A
Diode Forward Voltage	V _{SD}	—	-0.8	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	512	—	pF	V _{DS} = -30V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	31.3	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	23.2	—	pF	
Gate Resistance	R _g	—	11.9	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	4.0	—	nC	V _{DS} = -30V, I _D = -2A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	8.3	—	nC	
Gate-Source Charge	Q _{gs}	—	1.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.7	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	12.5	—	ns	V _{DD} = -30V, V _{GS} = -10V, I _D = -1.0A, R _G = 50Ω
Turn-On Rise Time	t _R	—	13.4	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	96.0	—	ns	
Turn-Off Fall Time	t _F	—	39.1	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	9.6	—	ns	I _F = -1A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	3.1	—	nC	I _F = -1A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

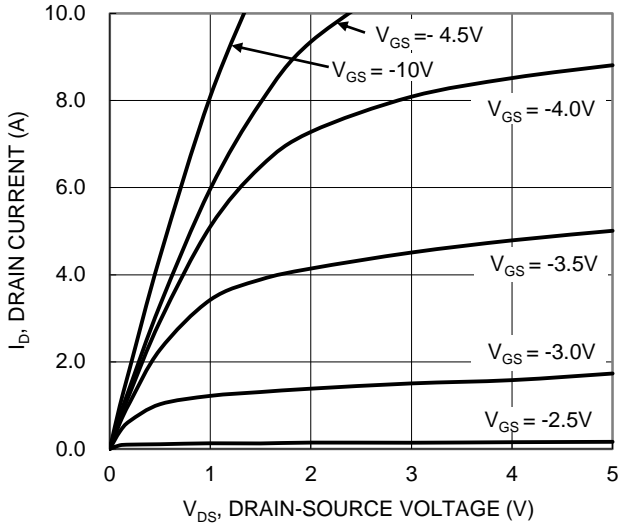


Figure 1. Typical Output Characteristic

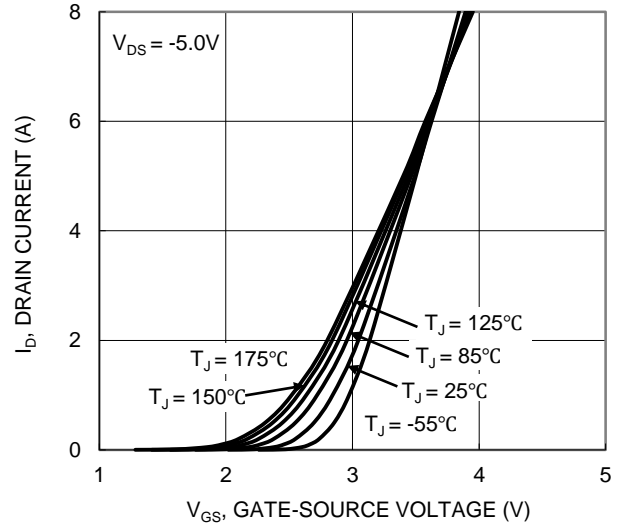


Figure 2. Typical Transfer Characteristic

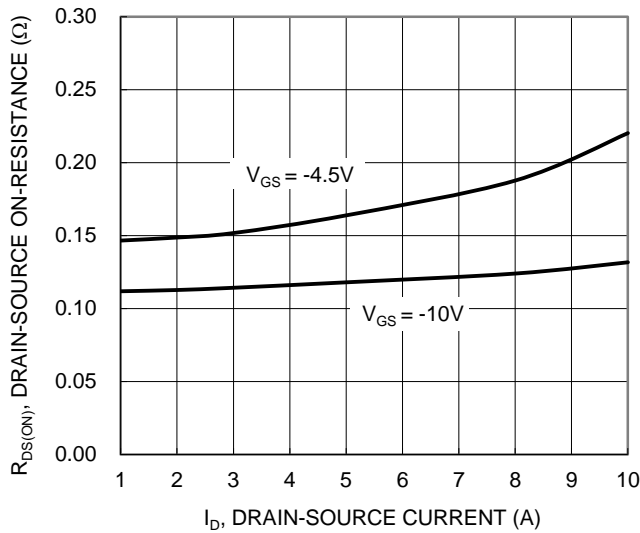


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

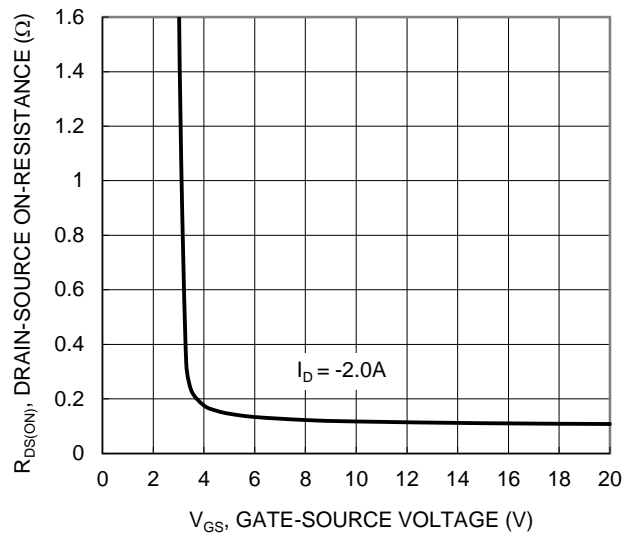


Figure 4. Typical Transfer Characteristic

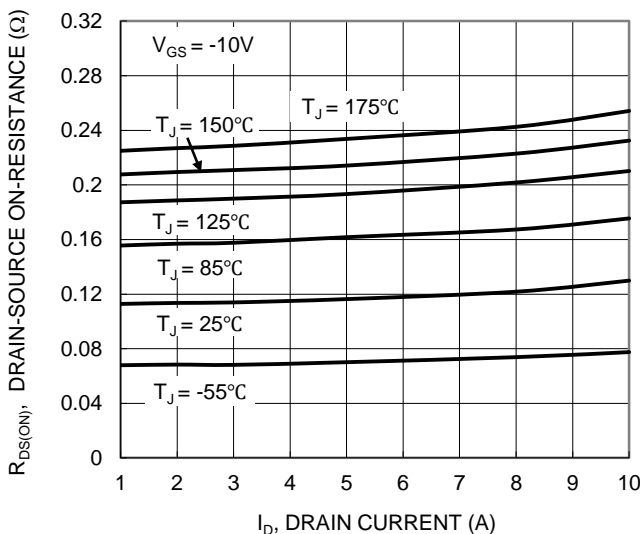


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

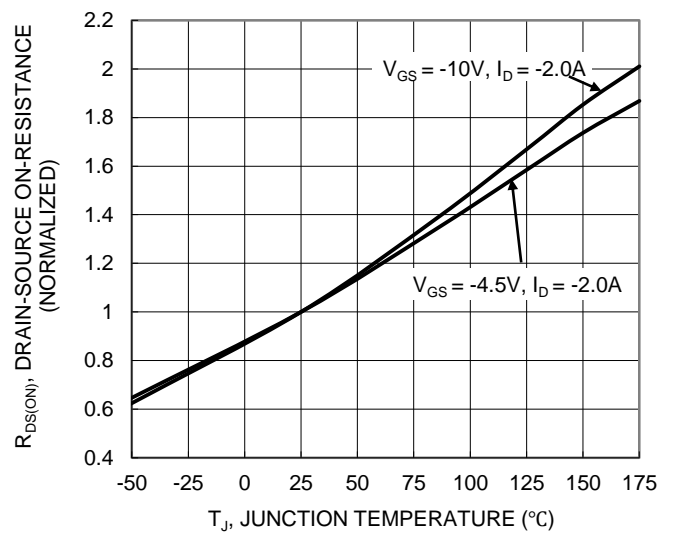
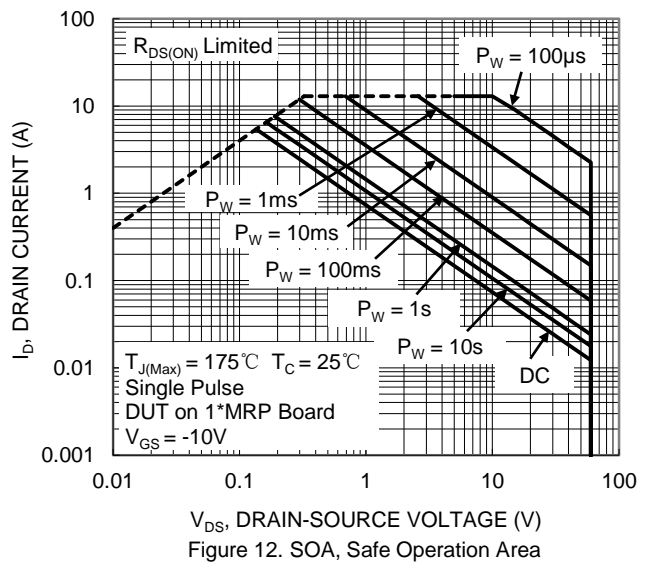
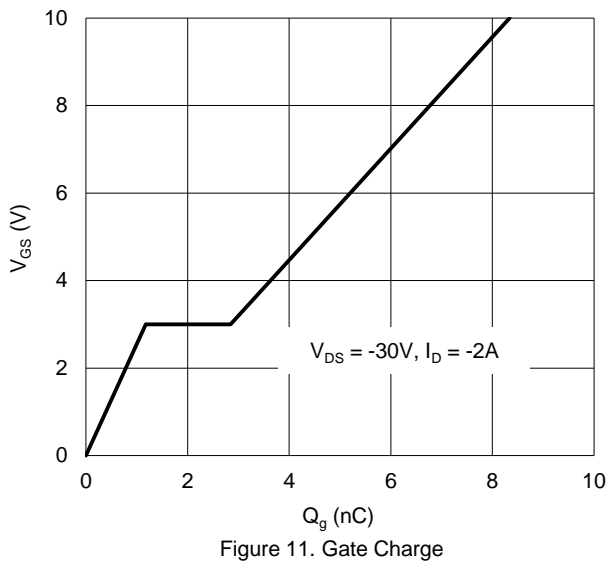
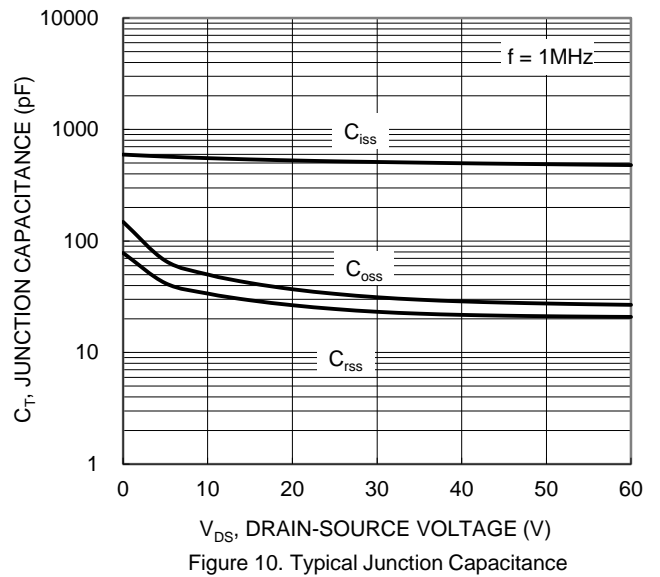
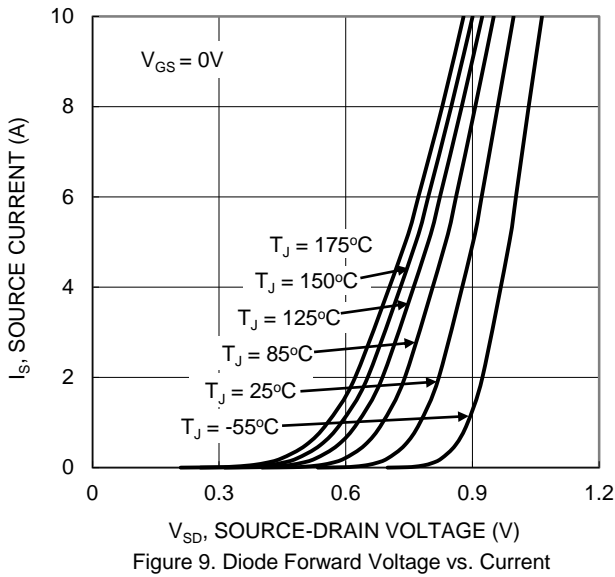
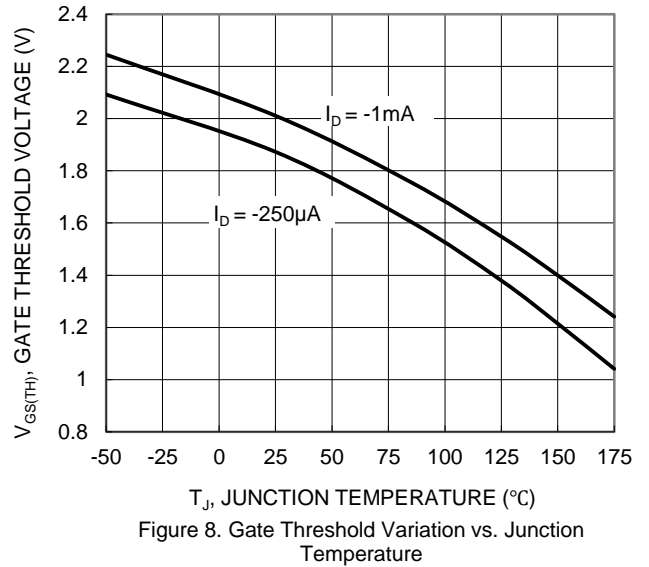
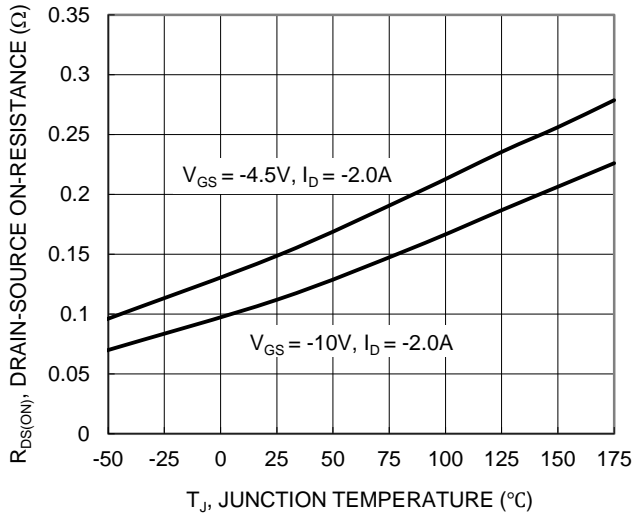


Figure 6. On-Resistance Variation with Temperature



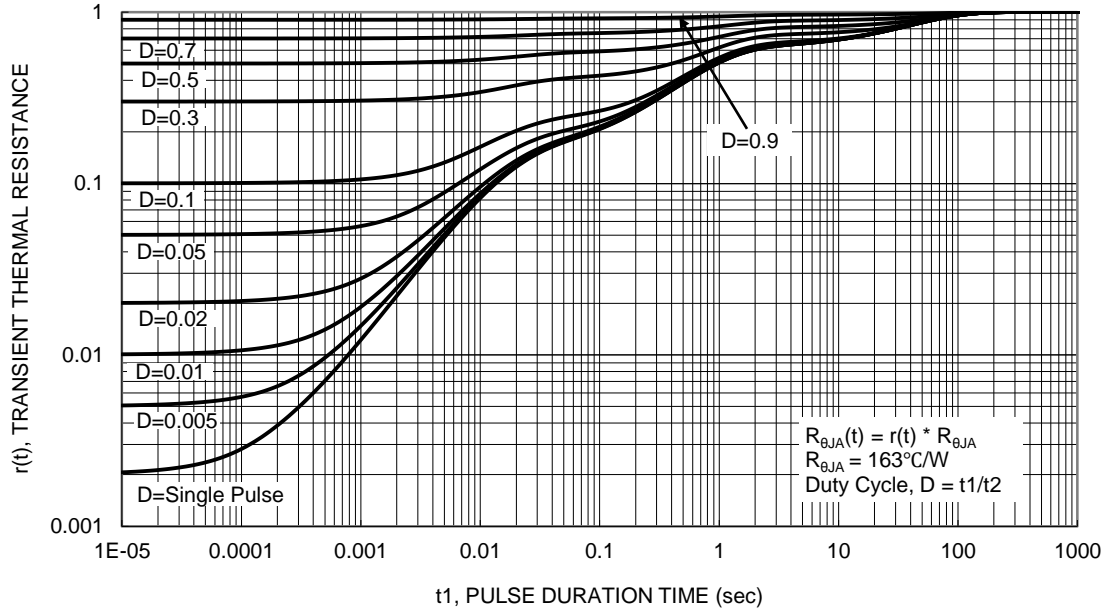
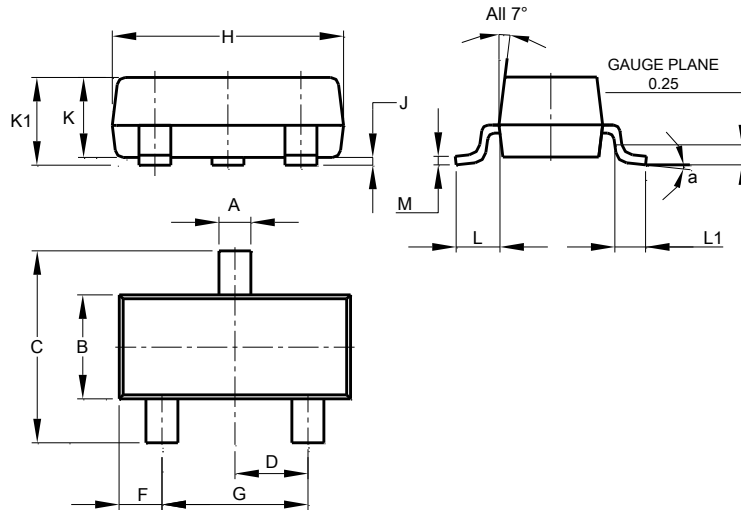


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

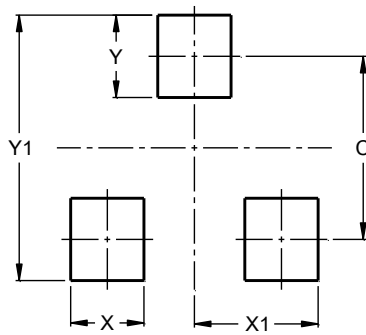


SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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